UP6202

150mA Low Power CMOS LDO

■ DESCRIPTION

The UP6202 series are a highly precise, lower consumption, 3 terminals, positive voltage regulators manufactured using CMOS and laser trimming technologies. The series provides large currents with a significantly small dropout voltage. The UP6202 consists of a current limiter circuit, a driver transistor, a precision reference voltage and an error correction circuit. The series is compatible with low ESR ceramic capacitors. The current limiter's foldback circuit operates as a short circuit protection as well as the output current limiter for the output pin. Output voltages are internally by laser trimming technologies. It is selectable in 0.1V increments within a range of 2.5V to 5.0V. UP6202 series are available in SOT23-3L packages

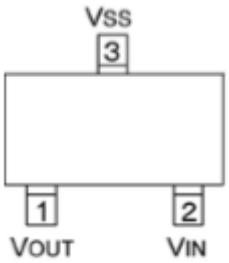
■ FEATURE

- ***Low power consumption***
- ***Low voltage drop***
- ***Low temperature coefficient***
- ***Quiescent current 2uA at 18V***
- ***High output current 150mA***
- ***Output voltage accuracy: tolerance 2%***
- ***SOT23-3L packages***

■ APPLICATIONS

- Battery-powered equipment
- Communication equipment
- Audio/Video equipment

■ PIN CONFIGURATION



SOT-23
(TOP VIEW)

■ PART NUMBER INFORMATION

UP6202-①②③④	① ②=Output Voltage 2.5V ~ 5.0V ③=Output Voltage Accuracy 2=2% ④=Package Code M=SOT23-3L

■ ORDERING INFROMATION

Part Number	Output Voltage	Package	Marking
UP6206-332M	3.3	SOT23-3L	3000EA / T&R

■ ABSOLUTE MAXIMUM RATINGS (T_A = 25℃ Unless otherwise noted)

Symbol	Parameter	Typical	Unit
$V_{IN(MAX)}$	Supply Voltage	20	V
I_{OUT}	Output Current	150	mA
V_{OUT}	Output Voltage	V_{SS}-0.3~V_{IN}+0.3	
T_J	Operation Junction Temperature	150	℃
T_{STG}	Storage Temperature Range	-55~+150	℃
T_{OPR}	Operation Temperature	-40~+80	℃

Note: Absolute maximum ratings are those values beyond which the device could be permanently damaged. Absolute maximum ratings are stress rating only and functional device operation is not implied

■ THERMAL DATA

Symbol	Parameter	Package	Max	Unit
P_D	Power Dissipation	SOT23-3L	0.3	W

■ ELECTRICAL CHARACTERISTICS(T_A=25℃ Unless otherwise noted)

Symbol	Parameter	Condition	Min	Typ	Max	Unit
V_{IN}	Input Voltage		3.5		18	V
V_{OUT}	Output Voltage	$V_{IN}=V_{OUT}+1V$ I_{OUT}=10mA	V_{OUT}*0.98		V_{OUT}*1.02	V
I_{OUT}	Output Current Note1	$V_{IN}=V_{OUT}+1V$		150		mA
ΔV_{OUT}	Load Regulation	$V_{IN}=V_{OUT}+1V$, 1mA≤I_{OUT}≤80mA		15	30	mV
V_{DIF}	Dropout Voltage Note2	Refer to the next table				
I_{SS}	Quiescent Current	No Load		2	5	uA
$\Delta V_{OUT}/\Delta V_{IN}*V_{OUT}$	Line Regulation	$V_{OUT}+1V≤V_{IN}≤18V$, I_{OUT}=30mA			0.2	%V
$V_{OUT}/(T_A*V_{OUT})$	Output Voltage Temperature Coefficiency	I_{OUT}=30mA 0℃≤T_A≤70℃		100		Ppm/℃
PSRR	PSRR	F=1KHz $V_{IN}=V_{OUT}+1V$		50		dB
I_{SHORT}	Short Circuit Current	$V_{IN}=V_{OUT}+1.5V$ $V_{OUT}=V_{SS}$		120		mA
I_{LIMIT}	Over Current Protection			250	300	mA

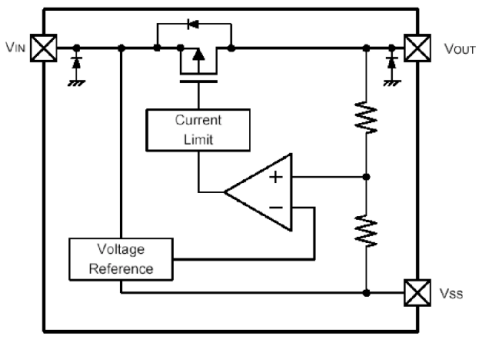
Note1: The deviation parameters V_{OUT} and I_{OUT} are defined as the difference between the maximum and minimum values obtained over the rated temperature range

Note2: $I_{OUT}=P_D/(V_{IN}-V_{OUT})$

Electrical characteristics by Output Voltage

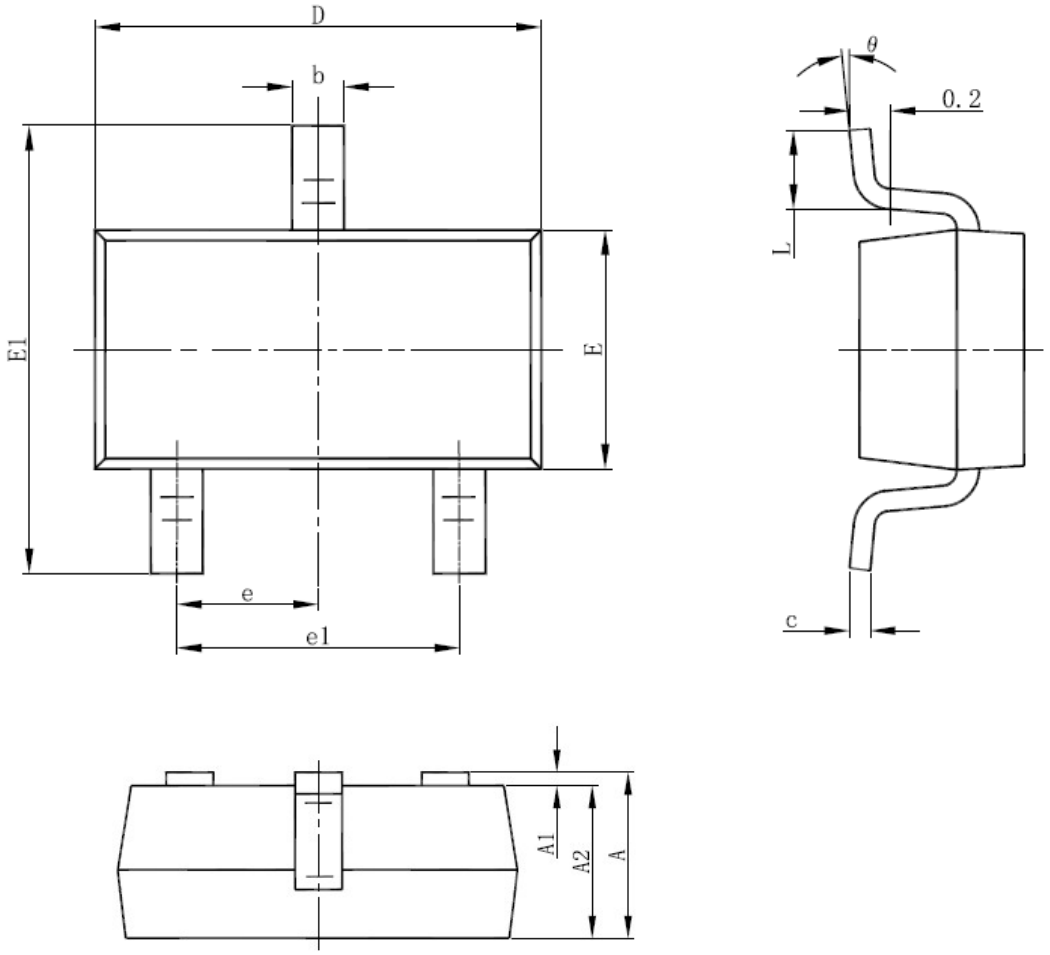
Output Voltage V_{OUT} (V)	Dropout Voltage Vdif (mV)		
	Conditions	Typ	Max
V_{OUT}≤3.0V	I_{OUT}=100mA	550	850
3.0V≤V_{OUT}≤4.0V		380	420
4.0V≤V_{OUT}≤5.0V		290	350

■ FUNCTION BLOCK DIAGRAM



*Diodes inside the circuit are an ESD protection diode and a parasitic diode.

■ SOT23 PACKAGE OUTLINE DIMENSIONS

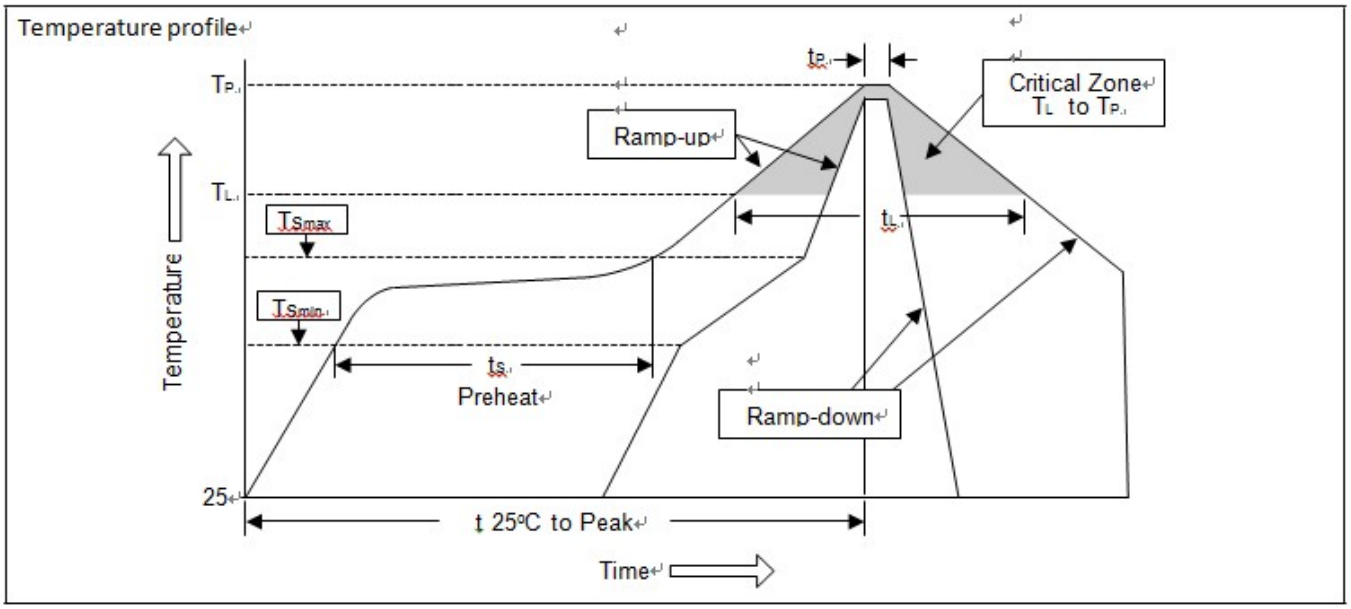


Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min	Max	Min	Max
A	1.050	1.250	0.041	0.049
A1	0.000	0.100	0.000	0.004
A2	1.050	1.150	0.041	0.045
b	0.300	0.500	0.012	0.020
c	0.100	0.200	0.004	0.008
D	2.820	3.020	0.111	0.119
E	1.500	1.700	0.059	0.067
E1	2.650	2.950	0.104	0.116
e	0.950(BSC)		0.037(BSC)	
e1	1.800	2.000	0.071	0.079
L	0.300	0.600	0.012	0.024
θ	0°	8°	0°	8°

■ SOLDERING METHODS FOR UNIVERCHIP

Storage environment Temperature=10℃~35℃ Humidity=65%±15%

Reflow soldering of surface mount device



Profile Feature	Sn-Pb Eutectic Assembly	Pb free Assembly
Average ramp-up rate (T_L to T_P)	<3℃/sec	<3℃/sec
Preheat -Temperature Min (T_{Smin}) -Temperature Max (T_{Smax}) -Time (min to max) (ts)	 100℃ 150℃ 60~120 sec	 150℃ 200℃ 60~180 sec
Tsmax to T_L -Ramp-up Rate	<3℃/sec	<3℃/sec
Time maintained above -Temperature (T_L) -Time (t_L)	 183℃ 60~150 sec	 217℃ 60~150 sec
Peak Temperature (T_P)	240℃+0/-5℃	260℃+0/-5℃
Time within 5℃ of actual Peak Temperature (t_P)	10~30 sec	20~40 sec
Ramp-down Rate	<6℃/sec	<6℃/sec
Time 25℃ to Peak Temperature	<6 minutes	<6 minutes

Flow (wave) soldering (solder dipping)

Product	Peak Temperature	Dipping Time
Pb device	245℃±5℃	5sec±1sec
Pb-Free device	260℃+0/-5℃	5sec±1sec

This integrated circuit can be damaged by ESD UniverChip Corporation recommends that all integrated circuits be handled with appropriate precautions. Failure to observe proper handling and installation procedure can cause damage. ESD damage can range from subtle performance degradation to complete device failure. Precision integrated circuits may be more susceptible to damage because very small parametric changes could cause the device not to meet its published specifications.